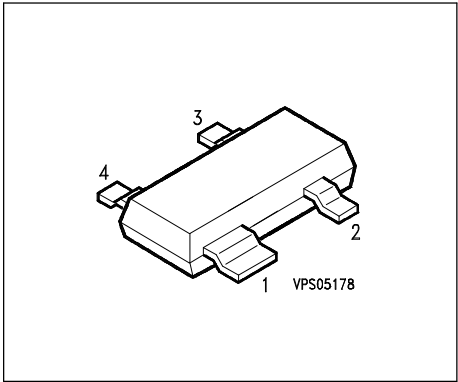


Silicon Schottky Diodes

- Zero bias diode array for mixer and detectors up to GHz frequencies
- Crossover ring quad



Type	Marking	Ordering Code	Pin Configuration			Package
BAT 63-099R	PSN	Q62702-A1105	1 = A	2 = C		SOT-143

Maximum Ratings

Parameter	Symbol	Values	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	40	mA
Total power dissipation, BAT17W $T_A \leq 97^\circ\text{C}$	P_{tot}		mW
Total power dissipation, BAT17-04...06W $T_S \leq 92^\circ\text{C}$	P_{tot}		
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}		
Storage temperature	T_{stg}	- 55 ... + 150	

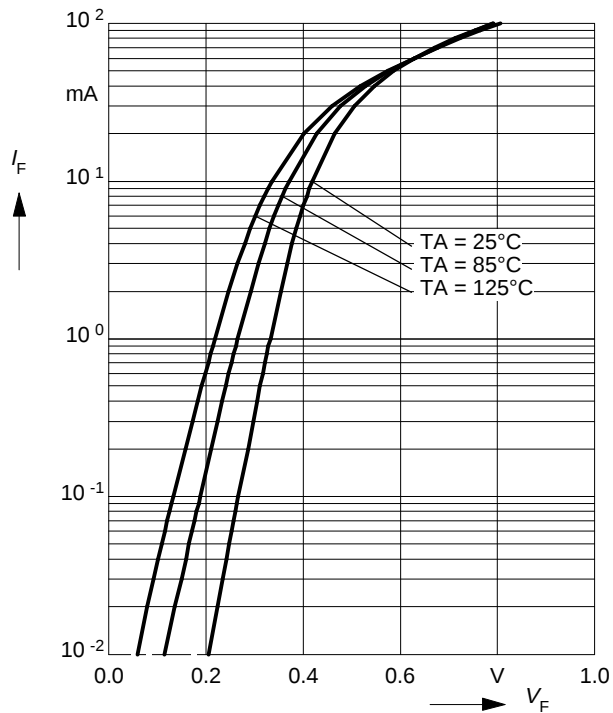
Thermal Resistance

Junction - ambient, BAT17W	R_{thJA}		K/W
Junction - ambient, BAT17-04W...06W	R_{thJA}		
Junction - soldering poin, BAT17W	R_{thJS}		
Junction - soldering point, BAT17-04W...06W	R_{thJS}		

Electrical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

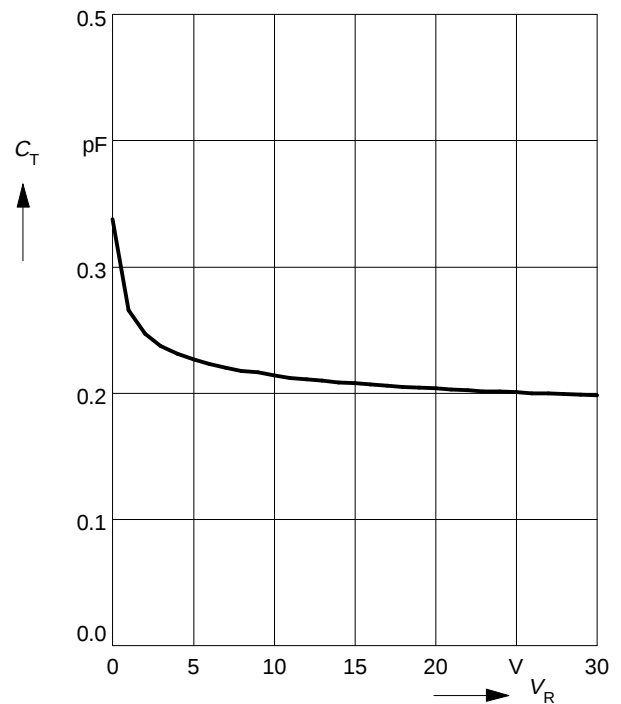
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Breakdown voltage $I_{\text{(BR)}} = 100\text{ }\mu\text{A}$	$V_{\text{(BR)}}$				V
Reverse current $V_{\text{R}} = 40\text{ V}$, $T_{\text{A}} = 25\text{ }^{\circ}\text{C}$	I_{R}	-	-	10	μA
Forward voltage $I_{\text{F}} = 2\text{ mA}$	V_{F}	-	0.85	1	V
Diode capacitance $V_{\text{R}} = 0$, $f = 1\text{ MHz}$	C_{T}	-	0.35	0.6	pF
Differential forward resistance $I_{\text{F}} = 5\text{ mA}$, $f = 100\text{ MHz}$	R_{F}				OHM

Forward current $I_F = f(V_F)$



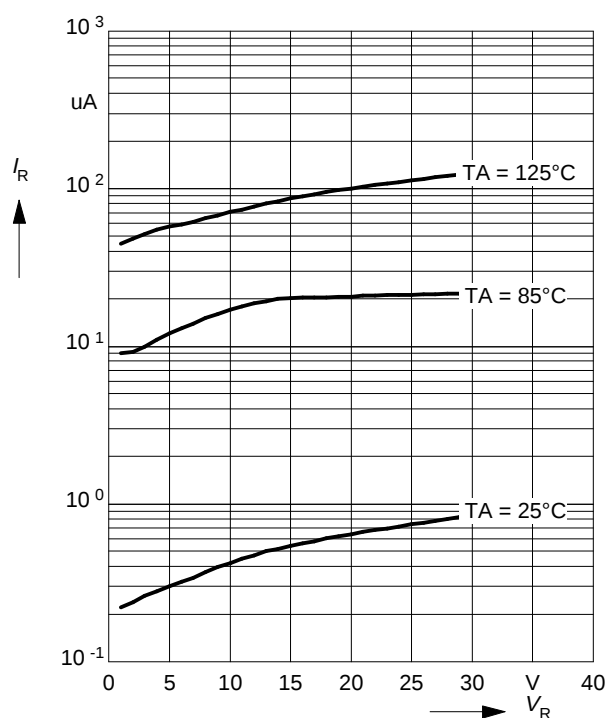
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Leakage current $I_R = f(V_R)$

$T_A = \text{Parameter}$



Package

